

TUNGSTEN SINTERED COMPACT SPUTTERING TARGET AND METHOD FOR PRODUCING SAME

ABSTRACT

5

Provided is a tungsten sintered compact sputtering target containing iron as an impurity in an amount of 0.8 wtppm or less, and remainder being tungsten and other unavoidable impurities, wherein a range of iron concentration in a target structure is within a range of ± 0.1 wtppm of an average concentration. Additionally provided is a tungsten sintered compact sputtering target according to claim 1 or claim 2, wherein a relative density of the target is 99% or higher, an average crystal grain size is 50 μm or less, and a crystal grain size range is 5 to 200 μm . The present invention aims to inhibit abnormal grain growth in the tungsten target by reducing the amount of iron in the tungsten sintered compact sputtering target.

10

15

Fig. 1